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# NTD4857N

## Power MOSFET 25 V, 78 A, Single N-Channel, DPAK/IPAK

### Features

- Trench Technology
- Low  $R_{DS(on)}$  to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- These are Pb-Free Devices

### Applications

- VCORE Applications
- DC-DC Converters
- Low Side Switching

**MAXIMUM RATINGS** ( $T_J = 25^\circ\text{C}$  unless otherwise stated)

Parameter		Symbol	Value	Unit
Drain-to-Source Voltage		$V_{DSS}$	25	V
Gate-to-Source Voltage		$V_{GS}$	$\pm 20$	V
Steady State	$T_A = 25^\circ\text{C}$	$I_D$	15	A
			11.7	
	$T_A = 25^\circ\text{C}$	$P_D$	2.1	W
	$T_A = 25^\circ\text{C}$	$I_D$	12	A
	$T_A = 85^\circ\text{C}$		9.3	
	$T_A = 25^\circ\text{C}$	$P_D$	1.31	W
	$T_C = 25^\circ\text{C}$	$I_D$	78	A
	$T_C = 85^\circ\text{C}$		61	
Pulsed Drain Current	$T_C = 25^\circ\text{C}$	$P_D$	56.6	W
	$t_p = 10\mu\text{s}$	$I_{DM}$	156	A
Current Limited by Package		$I_{DmaxPkg}$	45	A
Operating Junction and Storage Temperature		$T_J, T_{STG}$	-55 to +175	$^\circ\text{C}$
Source Current (Body Diode)		$I_S$	47	A
Drain to Source $dV/dt$		$dV/dt$	6	V/ns
Single Pulse Drain-to-Source Avalanche Energy ( $T_J = 25^\circ\text{C}$ , $V_{DD} = 50\text{ V}$ , $V_{GS} = 10\text{ V}$ , $I_L = 17\text{ A}_{pk}$ , $L = 1.0\text{ mH}$ , $R_G = 25\text{ }\Omega$ )		EAS	144.5	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		$T_L$	260	$^\circ\text{C}$

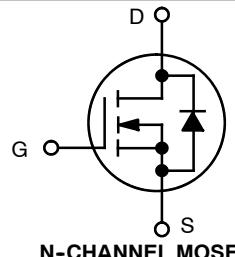
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



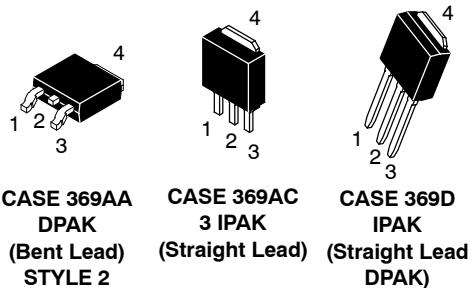
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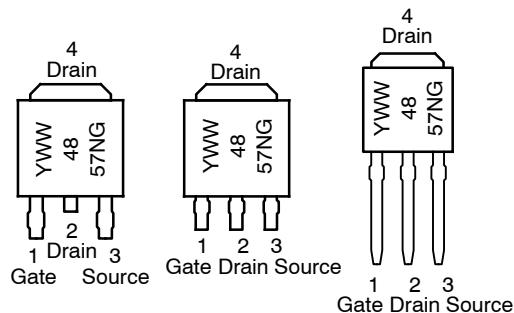
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
25 V	5.7 m $\Omega$ @ 10 V	
	8.0 m $\Omega$ @ 4.5 V	78 A



N-CHANNEL MOSFET



### MARKING DIAGRAMS & PIN ASSIGNMENTS



Y = Year  
WW = Work Week  
4857N = Device Code  
G = Pb-Free Package

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

## THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain)	$R_{\theta JC}$	2.65	$^{\circ}\text{C}/\text{W}$
Junction-to-TAB (Drain)	$R_{\theta JC-TAB}$	3.5	
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	72	
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	114.5	

1. Surface-mounted on FR4 board using 1 sq-in pad, 1 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size.

ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>							
Drain-to-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$		25			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(\text{BR})\text{DSS}}/T_J$				20		$\text{mV}/^{\circ}\text{C}$
Zero Gate Voltage Drain Current	$I_{\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}$ , $V_{\text{DS}} = 20 \text{ V}$	$T_J = 25^{\circ}\text{C}$			1.0	$\mu\text{A}$
			$T_J = 125^{\circ}\text{C}$			10	
Gate-to-Source Leakage Current	$I_{\text{GSS}}$	$V_{\text{DS}} = 0 \text{ V}$ , $V_{\text{GS}} = \pm 20 \text{ V}$				$\pm 100$	nA
<b>ON CHARACTERISTICS</b> (Note 3)							
Gate Threshold Voltage	$V_{\text{GS}(\text{TH})}$	$V_{\text{GS}} = V_{\text{DS}}$ , $I_D = 250 \mu\text{A}$		1.45		2.5	V
Negative Threshold Temperature Coefficient	$V_{\text{GS}(\text{TH})}/T_J$				5.3		$\text{mV}/^{\circ}\text{C}$
Drain-to-Source On Resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10 \text{ V}$	$I_D = 30 \text{ A}$		4.6	5.7	$\text{m}\Omega$
		$V_{\text{GS}} = 4.5 \text{ V}$	$I_D = 30 \text{ A}$		6.3	8.0	
Forward Transconductance	$g_{\text{FS}}$	$V_{\text{DS}} = 1.5 \text{ V}$ , $I_D = 15 \text{ A}$			77		S

## CHARGES AND CAPACITANCES

Input Capacitance	$C_{\text{ISS}}$	$V_{\text{GS}} = 0 \text{ V}$ , $f = 1.0 \text{ MHz}$ , $V_{\text{DS}} = 12 \text{ V}$		1960		pF
Output Capacitance	$C_{\text{OSS}}$			495		
Reverse Transfer Capacitance	$C_{\text{RSS}}$			265		
Total Gate Charge	$Q_{\text{G}(\text{TOT})}$	$V_{\text{GS}} = 4.5 \text{ V}$ , $V_{\text{DS}} = 15 \text{ V}$ , $I_D = 30 \text{ A}$		16	24	nC
Threshold Gate Charge	$Q_{\text{G}(\text{TH})}$			1.5		
Gate-to-Source Charge	$Q_{\text{GS}}$			5.7		
Gate-to-Drain Charge	$Q_{\text{GD}}$			6.6		
Total Gate Charge	$Q_{\text{G}(\text{TOT})}$		$V_{\text{GS}} = 10 \text{ V}$ , $V_{\text{DS}} = 15 \text{ V}$ , $I_D = 30 \text{ A}$	32		nC

## SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	$t_{\text{d}(\text{ON})}$	$V_{\text{GS}} = 4.5 \text{ V}$ , $V_{\text{DS}} = 15 \text{ V}$ , $I_D = 15 \text{ A}$ , $R_G = 3.0 \Omega$		13.9		ns
Rise Time	$t_r$			20.6		
Turn-Off Delay Time	$t_{\text{d}(\text{OFF})}$			18.6		
Fall Time	$t_f$			6.8		
Turn-On Delay Time	$t_{\text{d}(\text{ON})}$	$V_{\text{GS}} = 11.5 \text{ V}$ , $V_{\text{DS}} = 15 \text{ V}$ , $I_D = 15 \text{ A}$ , $R_G = 3.0 \Omega$		8.7		ns
Rise Time	$t_r$			18.7		
Turn-Off Delay Time	$t_{\text{d}(\text{OFF})}$			26		
Fall Time	$t_f$			3.6		

3. Pulse Test: pulse width  $\leq 300 \mu\text{s}$ , duty cycle  $\leq 2\%$ .
4. Switching characteristics are independent of operating junction temperatures.

# NTD4857N

## ELECTRICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS</b>							
Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 30 A	T <sub>J</sub> = 25°C		0.88	1.2	V
			T <sub>J</sub> = 125°C		0.74		
Reverse Recovery Time	t <sub>RR</sub>	V <sub>GS</sub> = 0 V, dI <sub>S</sub> /dt = 100 A/μs, I <sub>S</sub> = 30 A		11.7			ns
Charge Time	t <sub>a</sub>			7.2			
Discharge Time	t <sub>b</sub>			4.5			
Reverse Recovery Charge	Q <sub>RR</sub>			3.2			nC
<b>PACKAGE PARASITIC VALUES</b>							
Source Inductance	L <sub>S</sub>	T <sub>A</sub> = 25°C		2.49			nH
Drain Inductance, DPAK	L <sub>D</sub>			0.0164			
Drain Inductance, IPAK	L <sub>D</sub>			1.88			
Gate Inductance	L <sub>G</sub>			3.46			
Gate Resistance	R <sub>G</sub>			0.6			Ω

3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperatures.

## TYPICAL PERFORMANCE CURVES

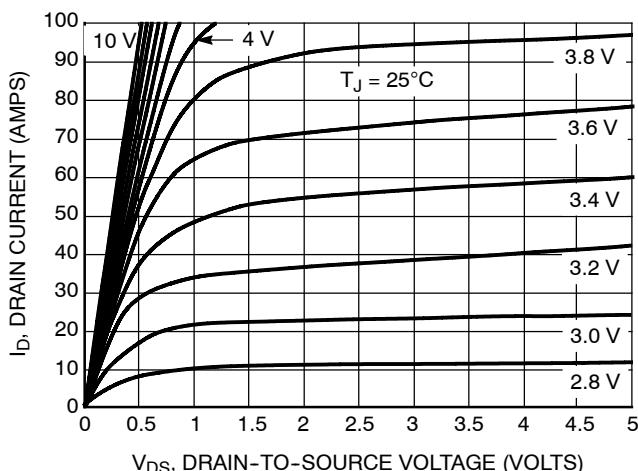


Figure 1. On-Region Characteristics

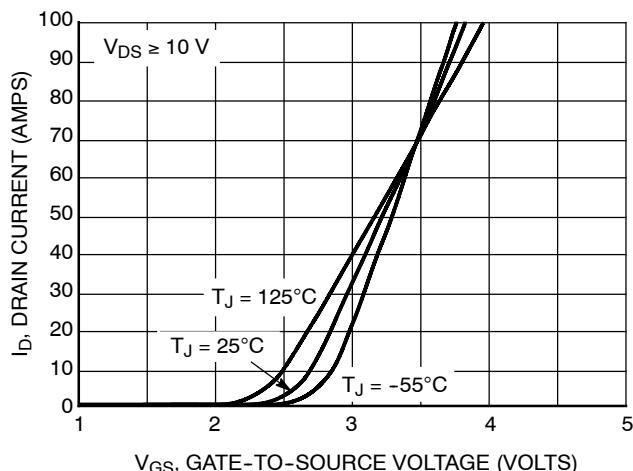


Figure 2. Transfer Characteristics

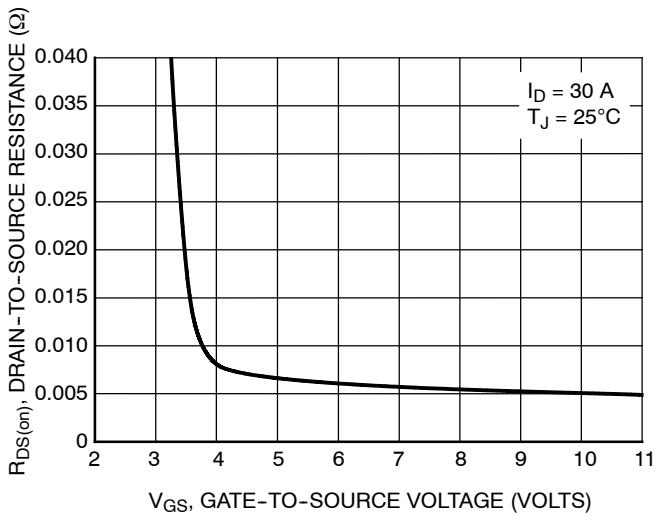


Figure 3. On-Resistance vs. Gate-to-Source Voltage

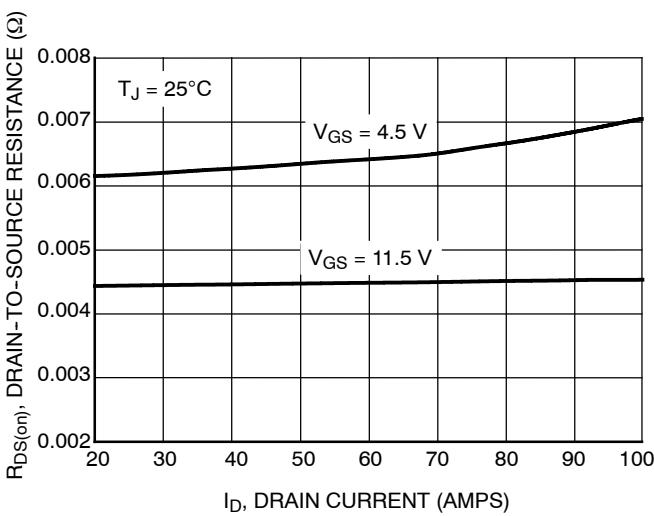


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

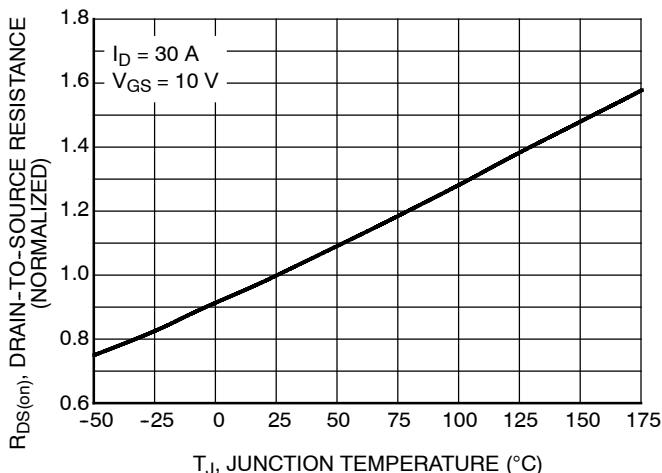


Figure 5. On-Resistance Variation with Temperature

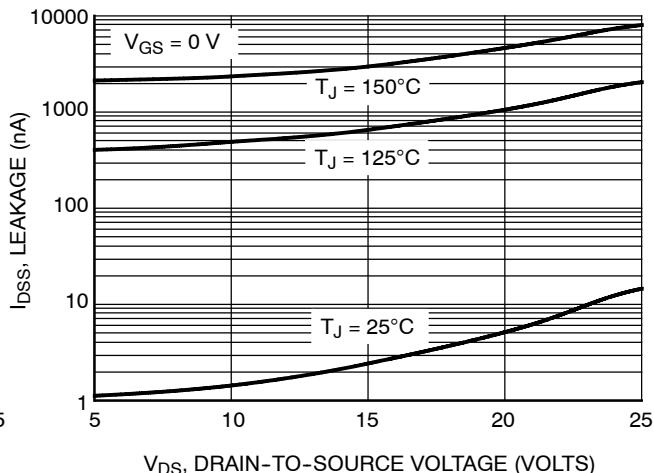


Figure 6. Drain-to-Source Leakage Current vs. Drain Voltage

## TYPICAL PERFORMANCE CURVES

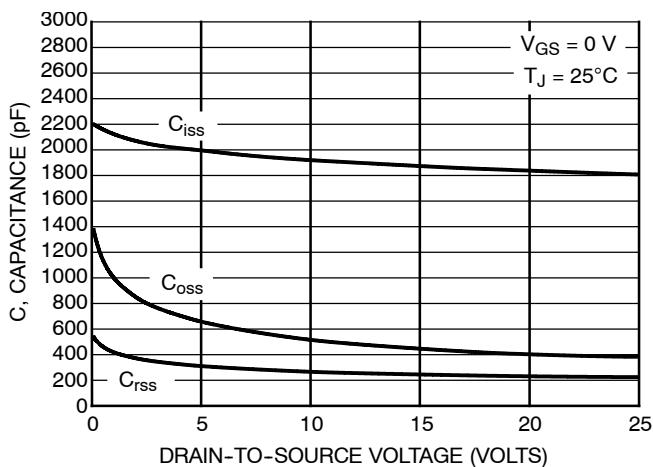


Figure 7. Capacitance Variation

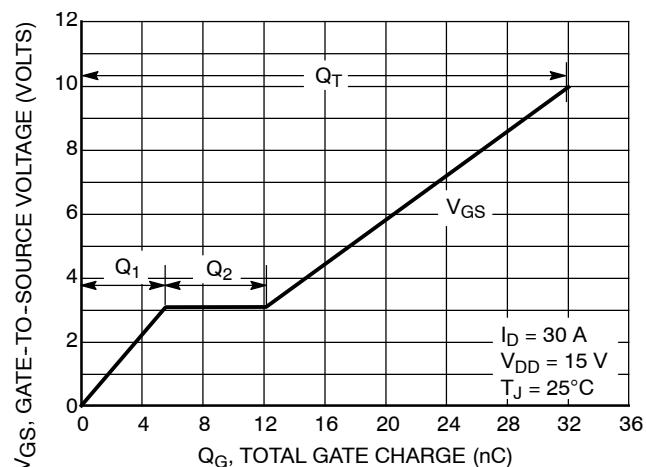


Figure 8. Gate-To-Source and Drain-To-Source Voltage vs. Total Charge

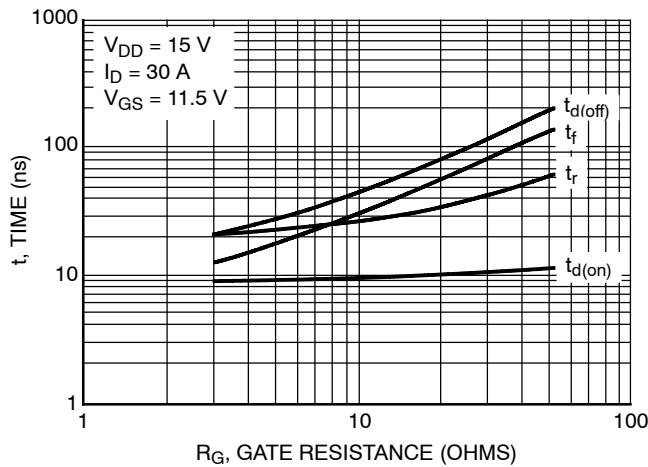


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

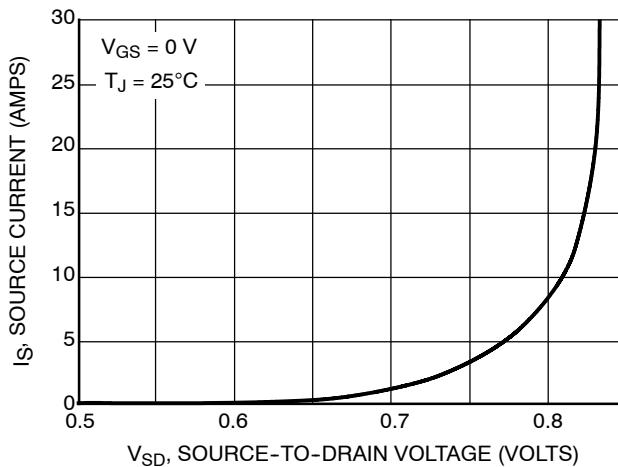


Figure 10. Diode Forward Voltage vs. Current

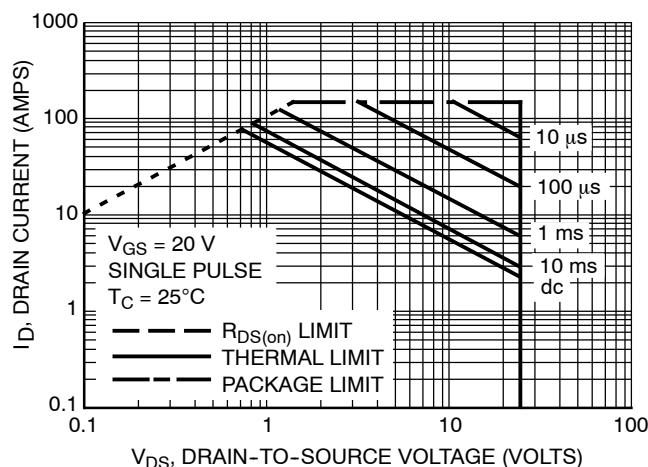


Figure 11. Maximum Rated Forward Biased Safe Operating Area

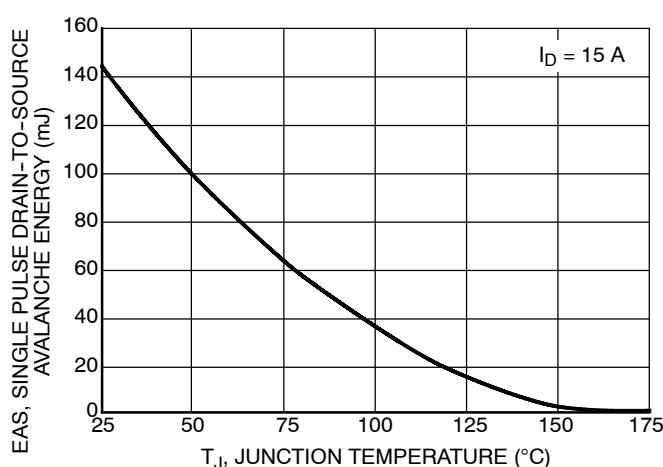


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

# NTD4857N

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
NTD4857NT4G	DPAK (Pb-Free)	2500 / Tape & Reel
NTD4857N-1G	IPAK (Pb-Free)	75 Units / Rail
NTD4857N-35G	IPAK Trimmed Lead ( $3.5 \pm 0.15$ mm) (Pb-Free)	75 Units / Rail

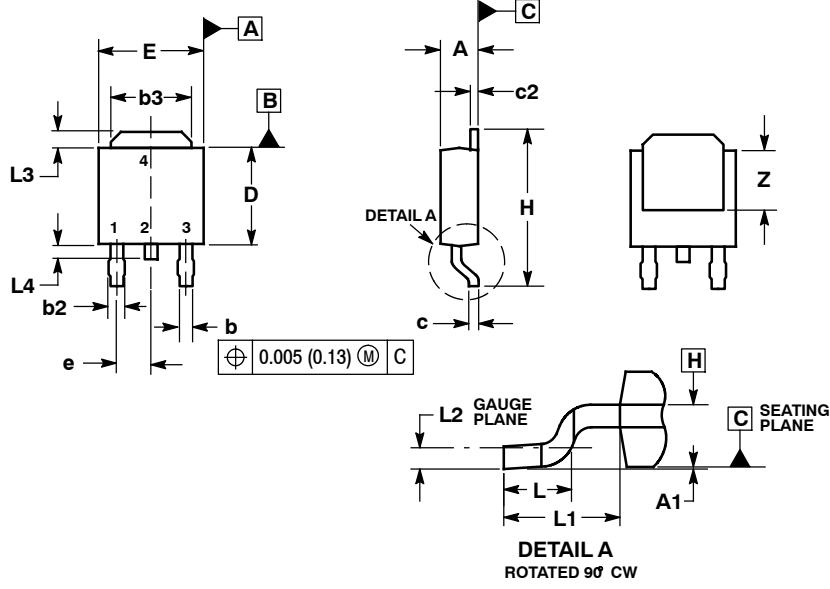
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## PACKAGE DIMENSIONS

## DPAK (SINGLE GUAGE)

CASE 369AA-01

ISSUE B

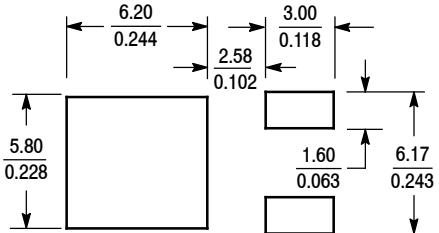


## NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108	REF	2.74	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

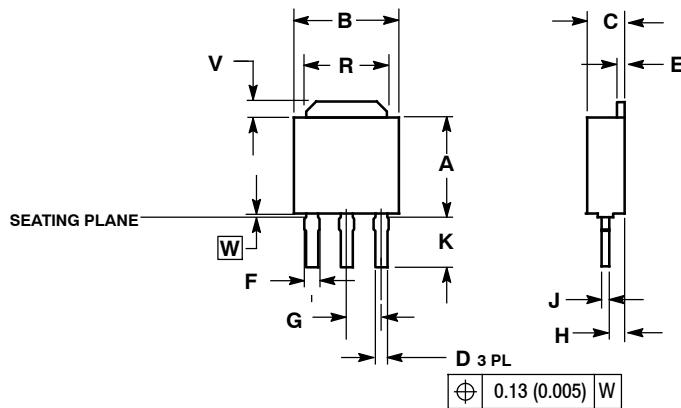
## SOLDERING FOOTPRINT\*

SCALE 3:1  $\left( \frac{\text{mm}}{\text{inches}} \right)$ 

STYLE 2:  
 PIN 1. GATE  
 2. DRAIN  
 3. SOURCE  
 4. DRAIN

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

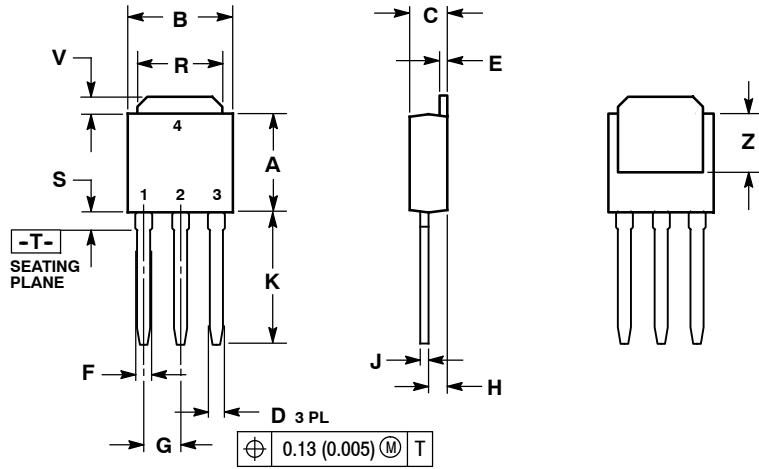
## PACKAGE DIMENSIONS

3 IPAK, STRAIGHT LEAD  
CASE 369AC-01  
ISSUE O

NOTES:

- 1.. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2.. CONTROLLING DIMENSION: INCH.
3. SEATING PLANE IS ON TOP OF DAMBAR POSITION.
4. DIMENSION A DOES NOT INCLUDE DAMBAR POSITION OR MOLD GATE.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.043	0.94	1.09
G	0.090	BSC	2.29	BSC
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.134	0.142	3.40	3.60
R	0.180	0.215	4.57	5.46
V	0.035	0.050	0.89	1.27
W	0.000	0.010	0.000	0.25

IPAK (STRAIGHT LEAD DPAK)  
CASE 369D-01  
ISSUE B

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090	BSC	2.29	BSC
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 2:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN

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